Non−inverting 1−to−2 Demultiplexer / Decoder

General Description

The ET74LVC1G19 is a high−performance non−inverting 1−to−2 demultiplexer. With the Select input [S] at Low, data at A is passed to Y0 and Y1 is set to high impedance. With the Select input [S] at High, data at A is passed to Y1 and Y0 is set to high impedance. The device operates over the voltage range from 1.65V to 5.5V.

This device has been optimized for on−board buffering applications and offers mixed (1.65V, 2.3V, 3.0V and 5.5V) voltage capability by providing over voltage tolerance (OVT) circuitry on I/O pins.

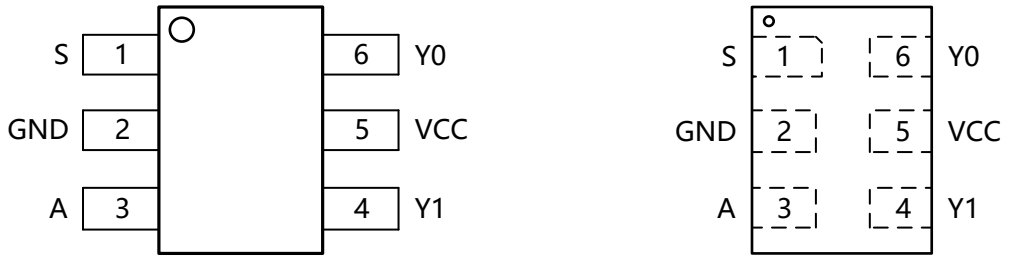
Features

- Designed for 1.65V to 5.5V VCC Operation
- High−Speed Propagation Delay t_{PD} 2.5nS (Typ)@3.3V, Load 50pF
- Power Down Impedance Outputs in High−Z
- Output Drive Capability 32mA
- These Devices are Pb−Free and are RoHS Compliant
- Packages are SC70-6,SOT23-6 or small DFN6
- MSL1 (DFN6) , MSL3(SC70-6,SOT23-6)

Device Information

Part No.	Package	Size
ET74LVC1G19	SC70-6	1.3mm×2.1mm
ET74LVC1G19T	SOT23-6	1.6mm×2.9mm
ET74LVC1G19Y	DFN6	1.0mm×1.5mm

Pin Configuration



SC70-6/SOT23-6 DFN6

Figure1. Pin Top View

Pin Function

Pin No.	Pin Name	Pin Function
1	S	Demultiplexer Select
2	GND	Ground
3	A	Data Input
4	Y1	Output 2
5	VCC	Power
6	Y0	Output 1

Block Diagram

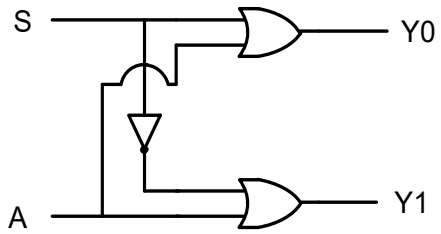


Figure2. Logic Symbol

Functional Description

Function Table

Input		Output	
A	**S**	**Y0=A+S**	**Y1=A+$\overline{S}$**
L	L	L	H
L	H	H	L
H	L	H	H
H	H	H	H

Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		-0.5 to 7.0	V
V_I	DC Input Voltage[1]		-0.5 ≤V_I ≤+7.0	V
V_O	DC Output Voltage Output in Higher or Low State		-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current V_I < GND		-50	mA
I_{OK}	DC Output Diode Current V_O < GND, V_O > V_{CC}		±50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Supply Pin		±100	mA
T_{STG}	Storage Temperature Range		-65 to 150	°C
T_L	Lead Temperature, Soldering 10 Seconds		260	°C
T_J	Max Junction Temperature		150	°C
V_{ESD}	ESD Classification	Human Body Model [2]	±4000	V
		Charged Device Model [3]	±1000	
I_{LU}	Max Latch up Current Above V_{CC} and GND at 125°C [4]		±100	mA

Stresses exceeding those listed in this table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note1. IO absolute maximum rating must be observed.

Note2. Tested to EIA/JESD22−A114−A.

Note3. Tested to JESD22−C101−A.

Note4. Tested to EIA/JESD78.

Thermal Characteristics

Symbol	Package	Ratings	Value	Unit
$R_{\theta JA}$	SC70-6	Thermal Characteristics, Thermal Resistance, Junction-to-Air	280	°C/W
	SOT23-6		180	
	DFN6(1.0×1.5)		440	
P_D	SC70-6	Power Dissipation in Still Air at 85°C	230	mW
	SOT23-6		360	
	DFN6(1.0×1.5)		150	

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		1.65	5.5	V
	Operating Date Retention		1.5	5.5	
V_{IN}	DC Input Voltage		0	5.5	V
V_{OUT}	DC Output Voltage(High or Low State)		0	5.5	V
T_A	Operating Temperature Range		-40	85	°C
t_r,t_f	Input Rise and Fall Time	V_{CC} = 2.5 V ± 0.2 V	0	20	ns/V
		V_{CC} = 3.0 V ± 0.3 V	0	10	
		V_{CC} = 5.0 V ± 0.5 V	0	5	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied.

Electrical Characteristics

DC Electrical Characteristics

Symbol	Parameter	Condition	V_{CC}(V)	T_A = 25°C			−40°C ≤T_A≤85°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		1.65-1.95 2.3-5.5	0.75Vcc 0.7Vcc			0.75Vcc 0.7Vcc		V
V_{IL}	Low−Level Input Voltage		1.65-1.95 2.3-5.5			0.25Vcc 0.3Vcc		0.25Vcc 0.3Vcc	V
V_{OH}	High−Level Output Voltage	I_{OH}=-100uA	1.65-5.5	Vcc−0.1	Vcc		Vcc−0.1		V
		I_{OH}=-3mA	1.65	1.29	1.52		1.29		
		I_{OH}=-8mA	2.3	1.9	2.1		1.9		
		I_{OH}=-12mA	2.7	2.2	2.4		2.2		
		I_{OH}=-16mA	3.0	2.4	2.7		2.4		
		I_{OH}=-24mA	3.0	2.3	2..5		2.3		
		I_{OH}=-32mA	4.5	3.8	4.0		3.8		
V_{OL}	Low−Level Output Voltage	I_{OL}=100uA	1.65-5.5		0.0	0.1		0.1	V
		I_{OL}=3mA	1.65		0.08	0.24		0.24	
		I_{OL}=8mA	2.3		0.20	0.3		0.3	
		I_{OL}=12mA	2.7		0.22	0.4		0.4	
		I_{OL}=16mA	3.0		0.28	0.4		0.4	
		I_{OL}=24mA	3.0		0.38	0.55		0.55	
		I_{OL}=32mA	4.5		0.42	0.55		0.55	
I_{IN}	Input Leakage Current	V_{IN}=5.5V or GND	0-5.5		±0.1			±1.0	uA

I_{OFF}	Power Off Leakage Current	V_{IN}=5.5V or V_{OUT}=5.5V	0			1		10	uA
I_{CC}	Quiescent Supply Current	V_{IN}=5.5V or GND	5.5					10	uA

AC Electrical Characteristics

$t_r = t_f$ = 2.5ns

Symbol	Parameter	Condition	V_{CC}(V)	T_A = 25°C			−40°C ≤T_A≤85°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay (Figure 3/4)	R_L= 1MΩ C_L= 15pF	1.65	2.0	5.3	11.4	2.0	12.0	ns
			1.8	2.0	4.4	9.5	2.0	10.0	
		R_L= 1MΩ C_L= 15pF	2.5±0.2	0.2	3.5	6.5	0.8	7.0	
		R_L= 1MΩ C_L= 15pF	3.3±0.3	0.8	2.1	4.5	0.5	4.7	
		R_L= 500Ω C_L =50pF		1.2	2.9	5.5	1.5	5.2	
		R_L= 1MΩ C_L= 15pF	5.0±0.5	0.5	1.8	3.9	0.5	4.1	
		R_L= 500Ω C_L=50pF		0.8	2.4	4.3	0.8	4.5	

Capacitive Characteristics

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC}= 5.5V, V_I = 0V or V_{CC}	>2.5	pF
C_{PD}	Power Dissipation Capacitance (5)	10MHz, V_{CC} = 3.3V, V_I = 0V or V_{CC}	9	pF
		10MHz, V_{CC} = 5.5V, V_I = 0V or V_{CC}	11	

Note5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)}=C_{PD}\times V_{CC}\times fin+I_{CC}\times C_{PD}$ is used to determine the no−load dynamic power consumption; $P_D=C_{PD}\times V_{CC}^2\times fin+I_{CC}\times V_{CC}\times Fig.$

Test Waveform

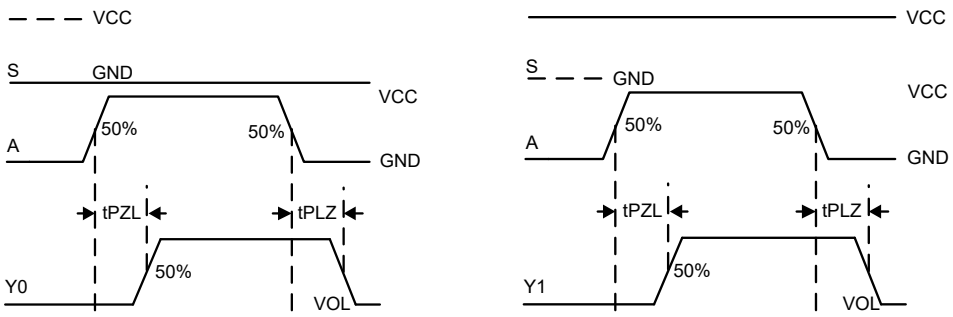


Figure 3/4 Switching Waveform

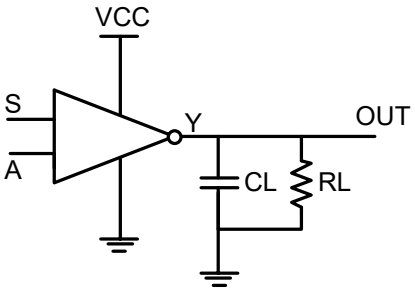
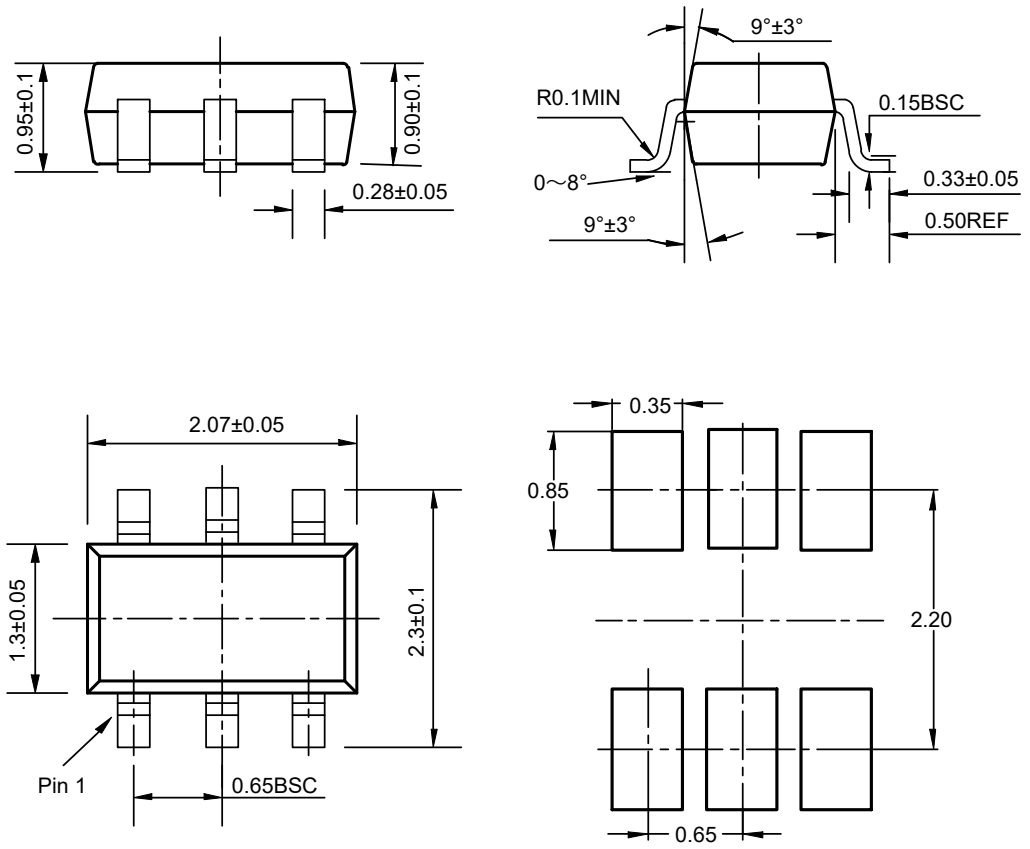


Figure 5. Test Circuit

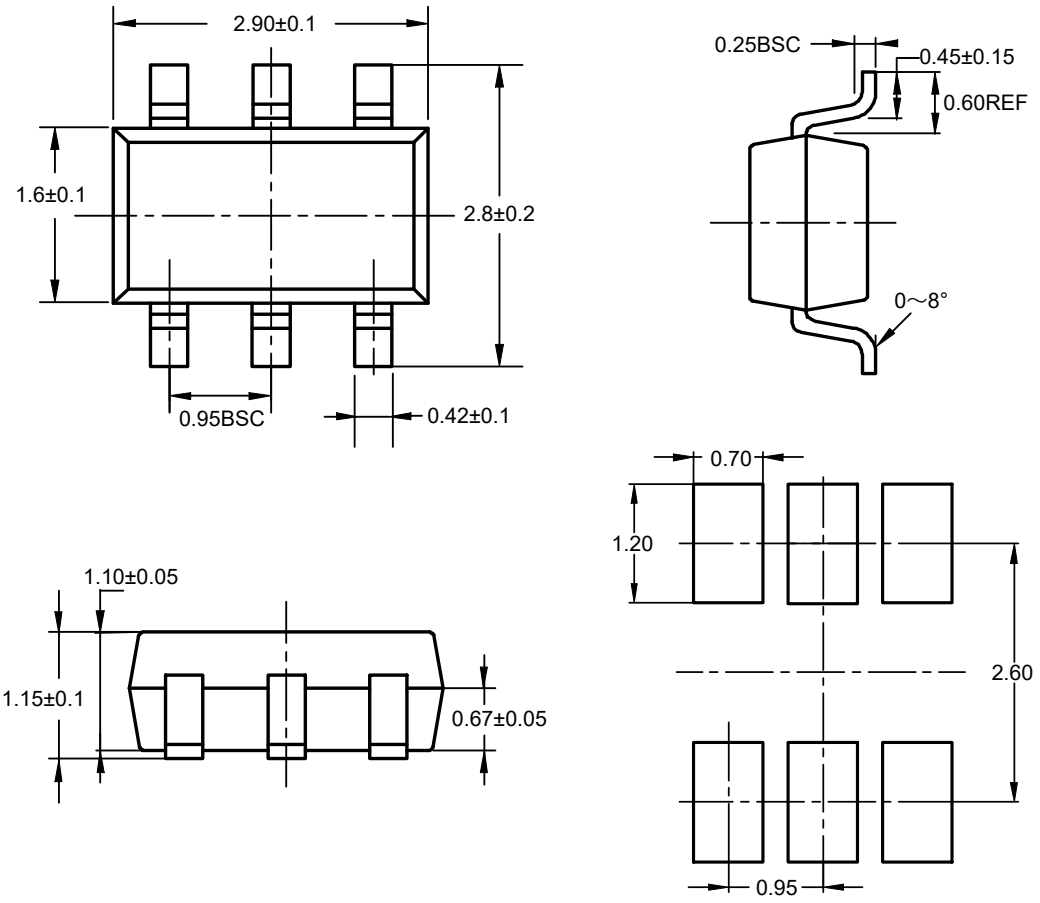
Package Dimension

SC70-6



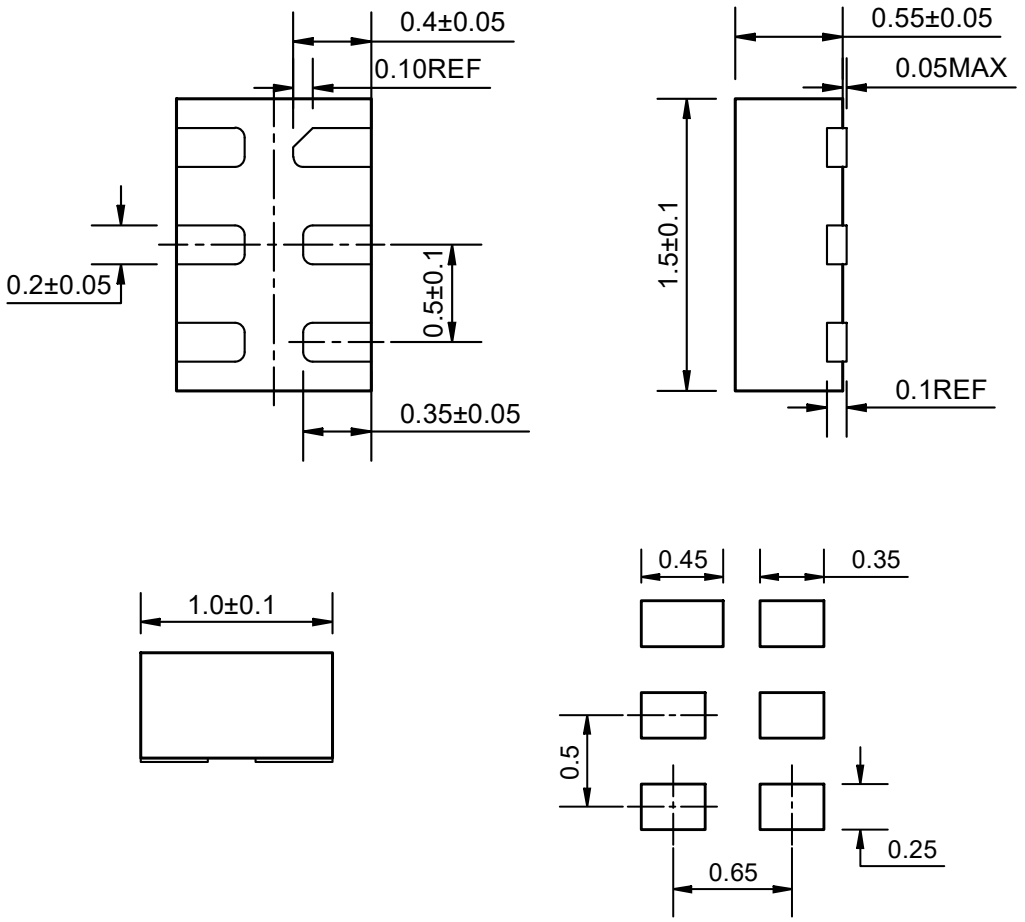
Recommended Land Pattern

SOT23-6



Recommended Land Pattern

DFN6



Recommended Land Pattern

Unit: mm

Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
1.0	2017-07-19	Original Version	Ma Yong jian	Ma Yong jian	Liu Jia Ying
1.1	2023-12-19	Update Typeset and Thermal Characteristics	Shibo	Shibo	Shibo